Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-9.   (Canceled)

10.   (Currently Amended)   A method for producing a single crystal by Czochralski method by pulling a seed crystal from a raw material melt, comprising:

immersing ~~a seed~~ the seed crystal into ~~a raw~~ the raw material melt; and

growing ~~a single~~ the single crystal by rotating and pulling the seed crystal, wherein:

the single crystal is pulled ~~with controlling~~ while controlling a value of V/G (mm^2/K • min) within a ~~determined~~ range of values of V/G (mm^2/K • min); and

the range of ~~a value~~ values of V/G (mm^2/K • min), including a ~~desired~~ defect region and/or a ~~desired~~ defect-free region, is ~~determined~~ controlled according to Tmax (°C); wherein:

V(mm/min) is ~~the single~~ a single crystal pulling rate of pulling ~~a single~~ the single crystal;

G (K/mm) is a temperature gradient at a solid-liquid interface, in a range of a melting point of the raw material and 1400°C;

Tmax (°C) is ~~the highest~~ a highest temperature of the raw material melt at an interface between a quartz crucible inner wall and ~~a raw~~ the raw material melt; and

the range of ~~a value~~ values of V/G (mm^2/K • min) is selected from ~~a~~ the group consisting of:

from -0.000724 [mm^2/(°C •K • min)] x Tmax (°C) + 1.31 (mm^2/K • min) to less than -0.000724 [mm^2/(°C •K • min)] x Tmax (°C) + 1.38 (mm^2/K • min);

$$-0.000724 \; [mm^2/(°C \cdot K \cdot min)] \times Tmax \; (°C) + 1.38$$

$(mm^2/K \cdot min)$ or more; and

$$from \; -0.000724 \; [mm^2/(°C \cdot K \cdot min)] \times Tmax \; (°C) + 1.31$$

$(mm^2/K \cdot min)$ to $-0.000724 \; [mm^2/(°C \cdot K \cdot min)] \times Tmax \; (°C) + 1.35 \; (mm^2/K \cdot min)$.

11-13. (Canceled)

14. (Previously Presented) The method for producing a single crystal according to Claim 10, wherein the single crystal is pulled with the Tmax (°C) being in a range of 1560 °C or less.

15-17. (Canceled)

18. (Previously Presented) The method for producing a single crystal according to Claim 10, wherein, at least, the Tmax (°C) is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

19-21. (Canceled)

22. (Previously Presented) The method for producing a single crystal according to Claim 14, wherein, at least, the Tmax (°C) is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

23-25. (Canceled)

26. (Currently Amended) The method of producing a single crystal according to Claim 10, wherein a silicon single crystal is pulled as the single crystal.crystal that is pulled is a silicon single crystal.

27. (Currently Amended) The method of producing a single crystal according to Claim 10, wherein a single the single crystal with that is pulled has a diameter of 200mm or more is pulled as the single crystal.more.

28.   (Canceled)